

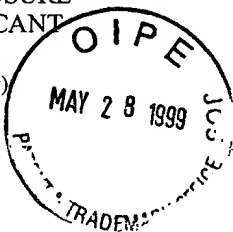
FORM PTO-1449 U.S. Department of Commerce
(Equivalent) Patent and Trademark Office

U.S. Application Serial No.
08/995,108

Atty. Docket No.
AM1776

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)



Peijun Ding et al.
Applicants

December 19, 1997
Filing Date

Unknown
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U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
<i>JM</i>	5,281,485	01/25/94	Colgan et al.	428	457	
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<i>JM</i>	EP 0 570 205 A1	11/18/93	Yamamoto et al.	H01L	21/321	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

JM Karen Holloway et al., "Tantalum as a Diffusion Barrier Between Copper and Silicon: Failure Mechanism and Effect of Nitrogen Additions", J. Appl. Phys. 71 (11), 1 June 1992, pp. 5433 - 5444.

JM Katsutaka Sasaki et al., "Stoichiometry of Ta-N Film and Its Application for Diffusion Barrier in the Al₃Ta/Ta-N/Si Contact System", Japanese Journal of Applied Physics, Vol. 29, No. 6, June 1990, pp. 1043 - 1047.

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Examiner: Juliana A. Maresca Date Considered 8/30/99

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U. S. PATENT DOCUMENTS

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<i>[Signature]</i>	4,319,264	03/09/82	Gangulee et al.	357	71	
<i>[Signature]</i>	5,186,718	02/16/93	Tepman et al.	29	25.01	
<i>[Signature]</i>	5,236,868	08/17/93	Nulman	437	190	
<i>[Signature]</i>	5,320,728	06/14/94	Tepman	204	192	
<i>[Signature]</i>	5,571,752	11/05/96	Chen et al.	437	189	

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U.S. Patent Application Serial No. 08/863,451, of Chiang et al., filed May 27, 1997.

U.S. Patent Application Serial No. 08/924,487, of Ngan et al., filed August 23, 1997.

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